

### Abstract of the Disclosure

The present invention is related to a stack gate electrode capable of suppressing a formation of a non-uniform silicide layer at an interface between a polysilicon layer and a metal layer during a selective oxidation process and a thermal process both being performed after a gate patterning process and a method for fabricating a semiconductor device including the same. The stack gate electrode includes: a silicon layer; a reaction prevention layer formed on the silicon layer, wherein the reaction prevention layer containing nitrogen and silicon has a surface density of nitrogen above about  $1 \times 10^{15}/\text{cm}^2$ ; and a metal layer formed on the reaction prevention layer.

15